

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A polycrystallization mask for laser illumination for converting amorphous silicon into polysilicon, the mask comprising:
a plurality of first transmissive areas slit having a first light transmittance;
a plurality of second transmissive areas slit having a second light transmittance different from the first light transmittance; and
an opaque area disposed at surroundings of the first and second transmissive slits, wherein the first and the second transmissive areas have shape of slits having width and length are isolated from each other by the opaque area.

2. (Currently Amended) The mask of claim 1, wherein the first transmissive areas include a slit is translucent film so that the first transmissive slit partly transmits light.

3. (Currently Amended) The mask of claim 2, wherein the second transmissive areas are openings slit is transparent so that the second transmissive slit completely transmits light.

4. (Currently Amended) The mask of claim 1, wherein the slits including mask includes a plurality of first transmissive slits and a plurality of second transmissive slits, the first and the second transmissive areas slits are arranged with a transverse pitch in a length moving direction of the mask and with a longitudinal pitch in a width-column direction to form a plurality of slit columns arranged with a second pitch substantially equal to half of the transverse pitch substantially perpendicular to the moving direction.

5. (Currently Amended) The mask of claim 4, wherein the first transmissive slits in adjacent two of the slit columns ~~are include~~ first column slits and second column slits, the first and second column slits being arranged in the column direction, each of the first column slits being offset to corresponding one of the second column slits by a half of the longitudinal pitch.

6. (Currently Amended) The mask of claim 5, wherein ~~each slit column includes either of the first transmissive areas and the second transmissive areas and the slit columns include first and second columns adjacent to each other and including the first transmissive areas and third and fourth columns adjacent to each other and including the second transmissive areas~~ slits include third column slits and fourth column slits, the third and fourth column slits being arranged in the column direction, each of the third column slits being offset to corresponding one of the fourth column slits by a half of the longitudinal pitch.

7. (Currently Amended) The mask of claim 6, wherein the ~~first, and the second, third and fourth columns and the column slits constitute first, second, third and the fourth columns, respectively, that are alternately sequentially arranged in the length-moving direction.~~

8. (Currently Amended) A polycrystallization mask for laser illumination for converting amorphous silicon into polysilicon, the mask comprising:

a plurality of first areas each including a plurality of first transmissive slit portions slits each having a first light transmittance, and the first transmissive slits being isolated from each other by a first opaque portion; and

a plurality of second areas each including a plurality of second transmissive slit portions-slits each having a second light transmittance, and the second transmissive slits being isolated from each other by a second opaque portion.

9. (Original) The mask of claim 8, wherein the first areas and the second areas are alternately arranged.

10. (Currently Amended) The mask of claim 8, wherein the first ~~slit portions~~ include a transmissive slits are translucent film so that the first transmissive slits partly transmit light.

11. (Currently Amended) The mask of claim 10, wherein the second ~~slit portions~~ include openings, transmissive slits are transparent so that the second transmissive slits completely transmit light.

12. (Currently Amended) The mask of claim 8, wherein the first and the second ~~slit portions~~ transmissive slits are arranged with a first pitch in a first direction, and the first or the second slit portions in each of the first and the second areas each include fifth and sixth slit portions, first and second sets of slits that are offset with to each other by a half of the first pitch in a second direction.

13. (Currently Amended) The mask of claim ~~8~~ 12, wherein the first ~~or the and~~ second slit portions in each of the first and the second areas sets of slits form two first and second slit columns, respectively, that are sequentially arranged in a second direction substantially perpendicular to the first direction.

14 - 20. (Canceled)

21. (New) The mask of claim 1, wherein the first transmissive slit has only the first light transmittance.

22. (New) The mask of claim 1, wherein the second transmissive slit has only the second light transmittance.

23. (New) The mask of claim 8, wherein the first transmissive slits each have only the first light transmittance.

24. (New) The mask of claim 8, wherein the second transmissive slits each have only the second light transmittance.